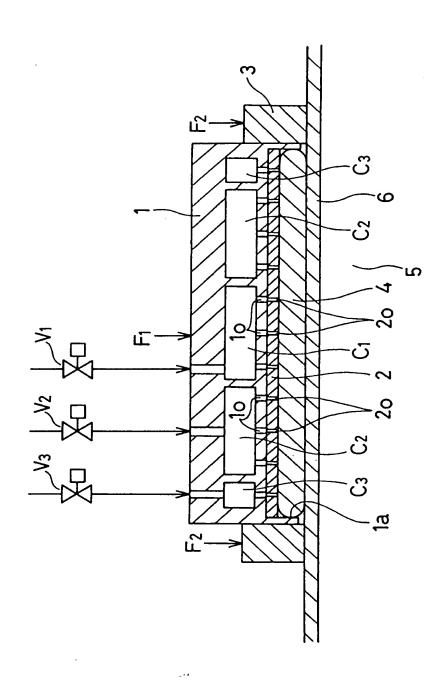
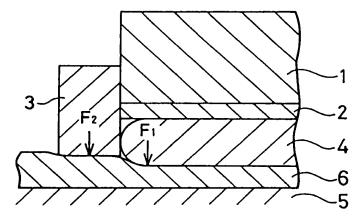
5762539

F1G.



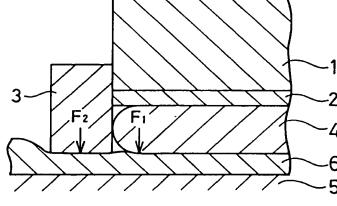
F / G. 2 A

 $\mathsf{F}\iota > \mathsf{F}_2$



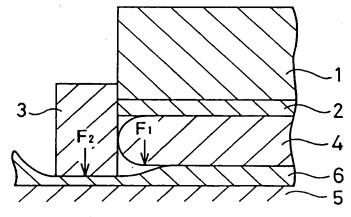
 $F_1 = F_2$

F / G. 2B



 $F_1 < F_2$

F 1 G. 2 C



O.G. FIG.

CLASS SUBCLASS

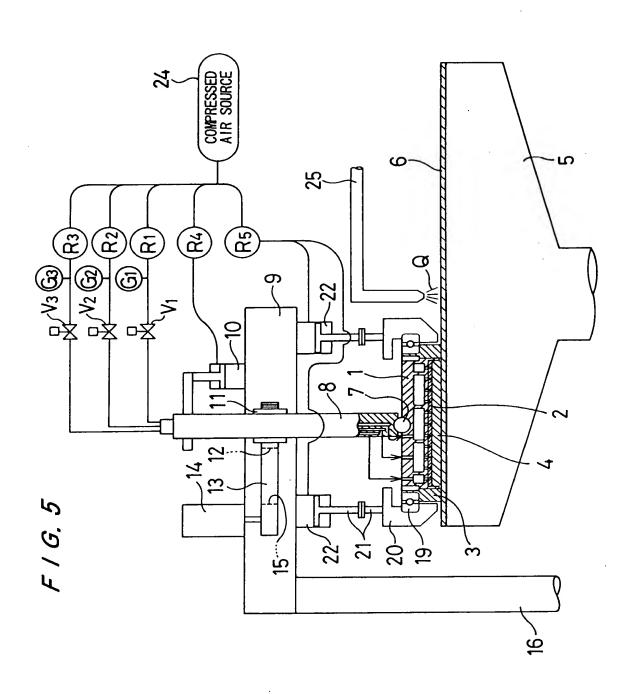
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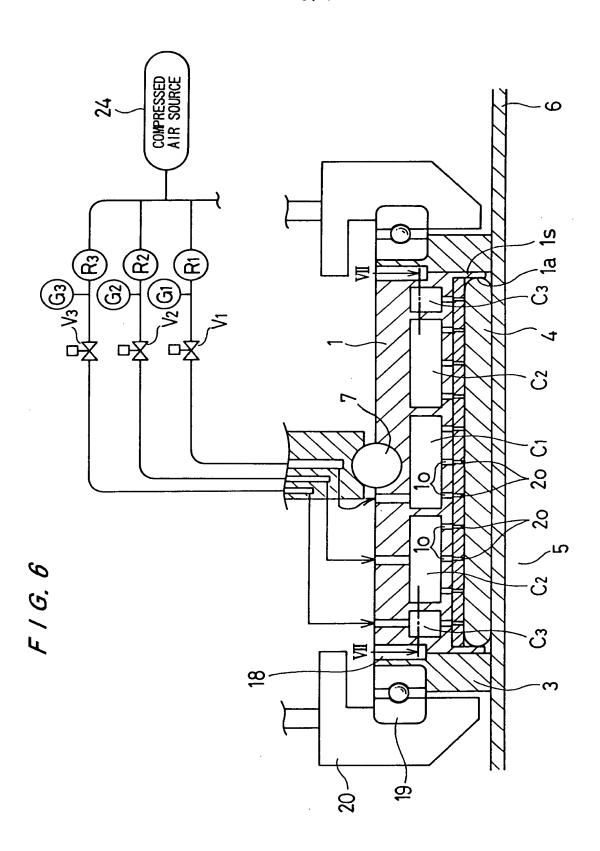
RAFTSHAM

3/8 2 2 DISTANCE FROM WAFER CENTER (mm) 30 F1G.3C \$ 22 09 02 8 8 THICKNESS OF REMOVED PRESSURE OF PRESSURIZED FLUID 20091/cm² **9** THE PRESSURIZED FLUID IS SUPPLIED ONLY TO THE FIRST CHAMBER C1 20 POLISHING PRESSURE 400gf/cm² DISTANCE FROM WAFER CENTER (mm) ဓ္ဌ F1G.3B \$ 22 09 02 8 8 8 MATÉRIAL (Å) MATERIAL (Å) 2 20 THE PRESSURIZED FLUID WAS NOT SUPPLIED 30 DISTANCE FROM WAFER CENTER (mm) F1G.34 9 22 99 2 8 8 2000 2000 2000 1000 1000 1000 WATERIAL (X)

F1G.4E 200 THICKNESS OF REMOVED MATERIAL (Å) F1G.4D DISTANCE FROM WAFER CENTER (mm) 8 900 8 ๅ็≅ THICKNESS OF REMOVED MATERIAL (Å) F1G.4C POLISHING PRESSURE:400gf/cm² DISTANCE FROM WAFER CENTER (mm) ន 6 8 CANCELLED 8 THICKNESS OF REMOVED MATERIAL (Å) 8 F1G.4B DISTANCE FROM WAFER CENTER (mm) 33 20 THICKNESS OF REMOVED MATERIAL (Å) 8 DISTANCE FROM WAFER CENTER (mm) F1G.4A 000 THICKNESS OF REMOVED MATERIAL (Å)

Zeran Estran





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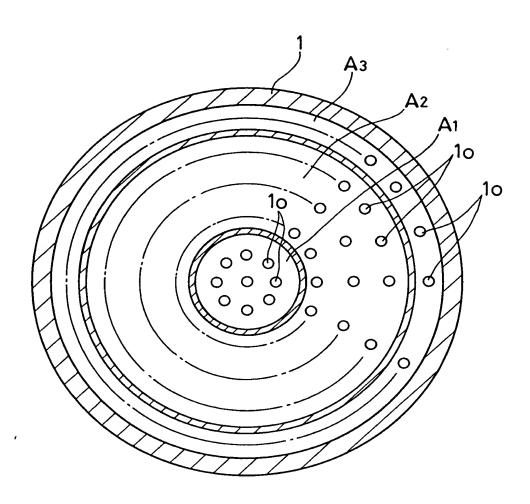
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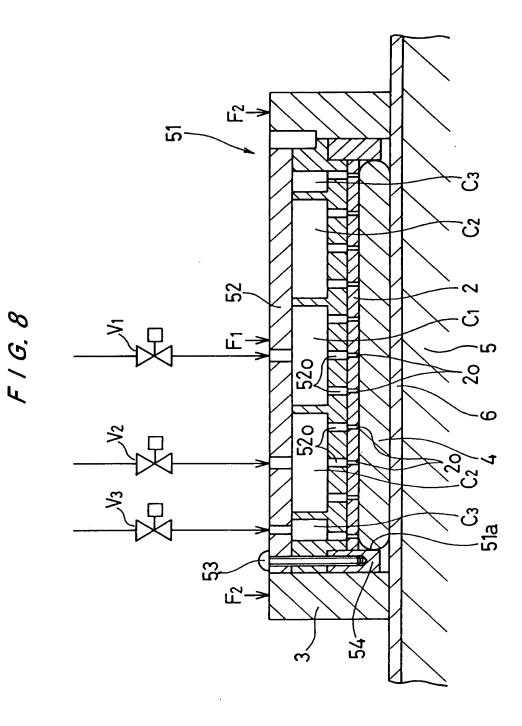
BY CLASS SUBCLASS

DRAFTSMAH

7/8

F / G. 7





DBBOY463 DEEVEL